

ABSTRACT OF THE DISCLOSURE

A method of depositing a low dielectric constant film on a substrate and post-treating the low dielectric constant film is provided. The post-treatment includes rapidly heating the low dielectric constant film to a desired high temperature and then rapidly cooling the low dielectric constant film such that the low dielectric constant film is exposed to the desired high temperature for about five seconds or less. In one aspect, the post-treatment also includes exposing the low dielectric constant film to an electron beam treatment and/or UV radiation.

250033